

KI SEMICONDUCTOR

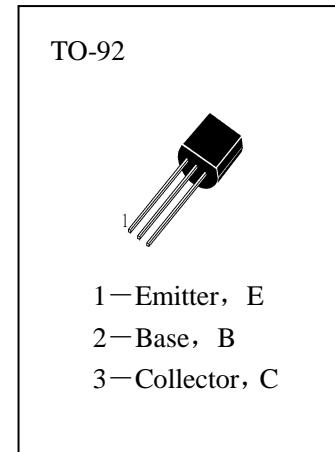
C1008

■ LOW FREQUENCY AMPLIFIER MEDIUM

SPEED SWITCHING

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

T_{stg} —Storage Temperature..... -55~150°C
 T_j —Junction Temperature..... 150°C
 P_C —Collector Dissipation..... 800mW
 V_{CBO} —Collector-Base Voltage..... 80V
 V_{CEO} —Collector-Emitter Voltage..... 60V
 V_{EBO} —Emitter-Base Voltage..... 8V
 I_C —Collector Current..... 700mA



■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

| Symbol | Characteristics | Min | Typ | Max | Unit | Test Conditions |
|---------------|---------------------------------------|-----|-------|------|------|---|
| I_{CBO} | Collector Cut-off Current | | | 100 | nA | $V_{CB}=60\text{V}$, $I_E=0$ |
| I_{EBO} | Emitter Cut-off Current | | | 100 | nA | $V_{EB}=5\text{V}$, $I_C=0$ |
| $HFE(1)$ | DC Current Gain | 40 | | 400 | | $V_{CE}=2\text{V}$, $I_C=50\text{mA}$ |
| $V_{CE(sat)}$ | Collector- Emitter Saturation Voltage | | 0. 2 | 0. 4 | V | $I_C=500\text{mA}$, $I_B=50\text{mA}$ |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | | 0. 86 | 1. 1 | V | $I_C=500\text{mA}$, $I_B=50\text{mA}$ |
| BV_{CBO} | Collector-Base Breakdown Voltage | 80 | | | V | $I_C=100 \mu\text{A}$, $I_E=0$ |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | 60 | | | V | $I_C=10\text{mA}$, $I_B=0$ |
| BV_{EBO} | Emitter-Base Breakdown Voltage | 8 | | | V | $I_E=10 \mu\text{A}$, $I_C=0$ |
| f_T | Current Gain-Bandwidth Product | 30 | 50 | | MHz | $V_{CE}=10\text{V}$, $I_C=50\text{mA}$ |
| C_{ob} | Output Capacitance | | 8 | | pF | $V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$ |

■ hfe Classification

R

O

Y

GR

40—80

70—140

120—240

240—400

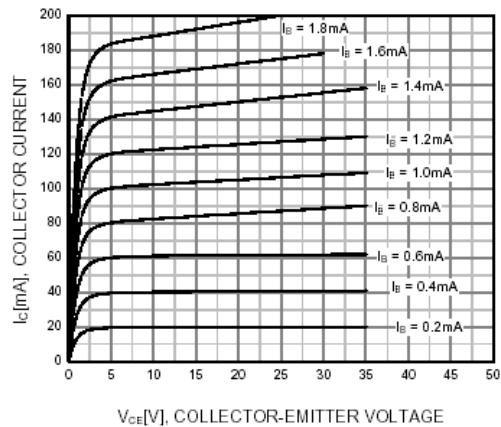


Figure 1. Static Characteristic

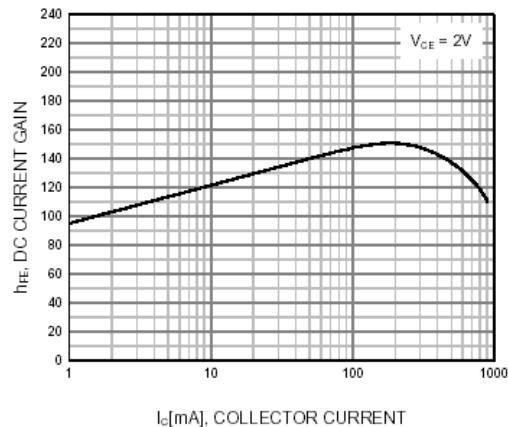


Figure 2. DC current Gain

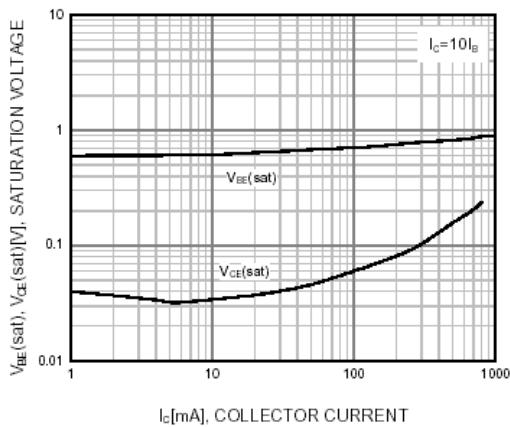


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

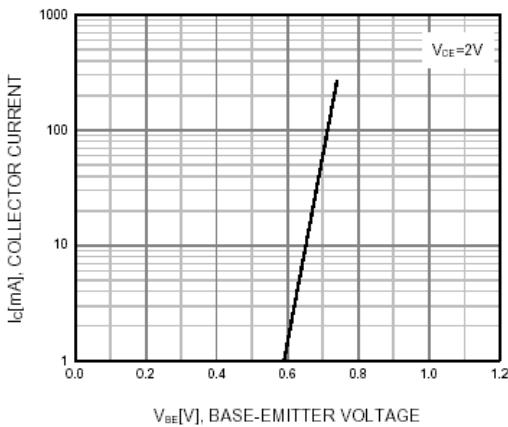


Figure 4. Base-Emitter On Voltage

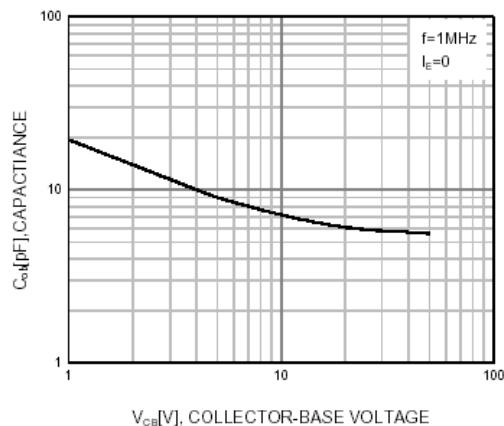


Figure 5. Collector Output Capacitance